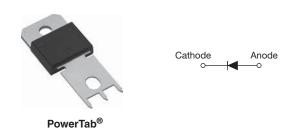


Ultrafast Soft Recovery Diode, 80 A FRED Pt®



| PRODUCT SUMMARY | | | | |
|----------------------------------|-----------------------|--|--|--|
| Package | PowerTab [®] | | | |
| I _{F(AV)} | 80 A | | | |
| V_{R} | 200 V | | | |
| V _F at I _F | 1.13 V | | | |
| t _{rr} (typ.) | See recovery table | | | |
| T _J max. | 175 °C | | | |
| Diode variation | Single die | | | |

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- Designed and qualified according to JEDEC-JESD47
- Compliant to RoHS Directive 2002/95/EC
- PowerTab[®] package





BENEFITS

- Reduced RFI and EMI
- · Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

| ABSOLUTE MAXIMUM RATINGS | | | | |
|---|-----------------------------------|-------------------------|-------------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MAX. | UNITS |
| Cathode to anode voltage | V_{R} | | 200 | V |
| Continuous forward current | I _{F(AV)} | T _C = 112 °C | 80 | |
| Single pulse forward current | I _{FSM} | T _C = 25 °C | 800 | Α |
| Maximum repetitive forward current | I _{FRM} | Square wave, 20 kHz | 160 | |
| Operating junction and storage temperatures | T _J , T _{Stg} | | - 55 to 175 | °C |

| ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified) | | | | | | |
|--|-------------------------------------|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage | V _{BR} , V _r | I _R = 50 μA | 200 | - | - | |
| Forward voltage V _F | V | I _F = 80 A | - | 0.98 | 1.13 | V |
| | VF | I _F = 80 A, T _J = 175 °C | - | 0.79 | 0.92 | |
| Develope legistre summer | $V_R = V_R$ rated | - | - | 50 | μA | |
| Reverse leakage current I _R | | T _J = 150 °C, V _R = V _R rated | - | - | 2 | mA |
| Junction capacitance | C _T | V _R = 200 V | | 89 | - | pF |
| Series inductance | L _S | Measured lead to lead 5 mm from package body | - | 3.5 | - | nH |



| DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified) | | | | | | | |
|---|---------------------------------------|--|--|------|------|------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNITS |
| | | $I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ | | - | - | 35 | |
| Reverse recovery time | Reverse recovery time t _{rr} | T _J = 25 °C | $I_F = 80 \text{ A}$ $V_R = 160 \text{ V}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ | - | 32 | - | ns |
| | | T _J = 125 °C | | - | 52 | - | |
| Peak recovery current I _{RRM} | | T _J = 25 °C | | - | 4.4 | - | Α |
| | IRRM | T _J = 125 °C | | - | 8.8 | - | |
| Reverse recovery charge Q _{rr} | 0 | T _J = 25 °C | | - | 70 | - | nC |
| | T _J = 125 °C | 1 | - | 240 | - | IIC | |

| THERMAL - MECHANICAL SPECIFICATIONS | | | | | | |
|--|-------------------|--|-------------|------|-------------|---------------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNITS |
| Thermal resistance, junction to case | R _{thJC} | | - | - | 0.70 | K/W |
| Thermal resistance, junction to heatsink | R _{thCS} | Mounting surface, flat, smooth and greased | - | 0.2 | - | N/VV |
| Woight | | | - | - | 5.02 | g |
| Weight | | | - | 0.18 | - | OZ. |
| Mounting torque | | | 1.2 (10) | - | 2.4 (20) | N · m (lbf · in) |
| Marking device | | Case style PowerTab® | | 80EF | 3U02 | • |



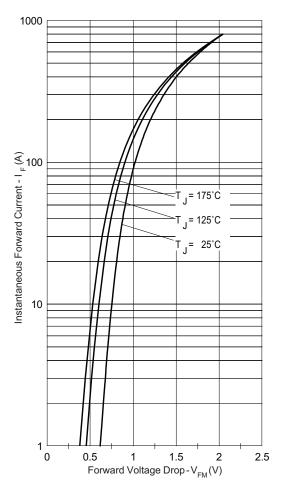


Fig. 1 - Maximum Forward Voltage Drop Characteristics

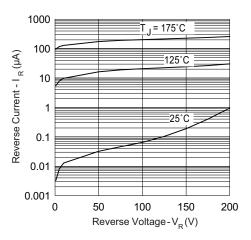


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

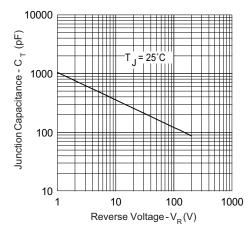


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

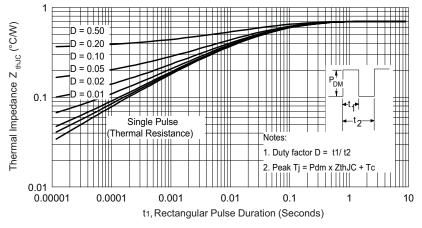


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

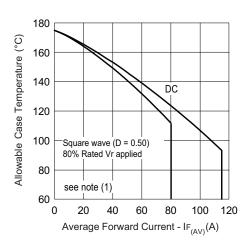


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

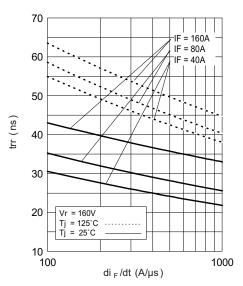


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

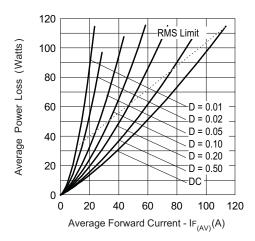


Fig. 6 - Forward Power Loss Characteristics

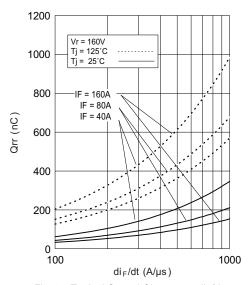


Fig. 8 - Typical Stored Charge vs. dI_F/dt

Note

 $\begin{array}{ll} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at} \ (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ \text{(1 - D)}; \ I_R \ \text{at} \ V_{R1} = 80 \ \% \ \text{rated} \ V_R \\ \end{array}$



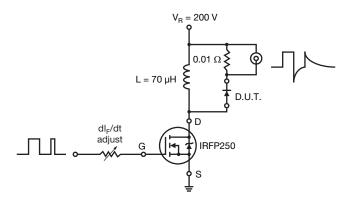
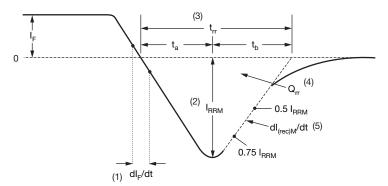


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) ${\rm Q_{rr}}$ area under curve defined by ${\rm t_{rr}}$ and ${\rm I_{RRM}}$

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

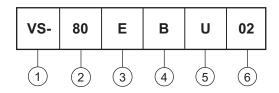
(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (80 = 80 A)

3 - Single diode

4 - PowerTab[®] (ultrafast/hyperfast only)

5 - Ultrafast recovery

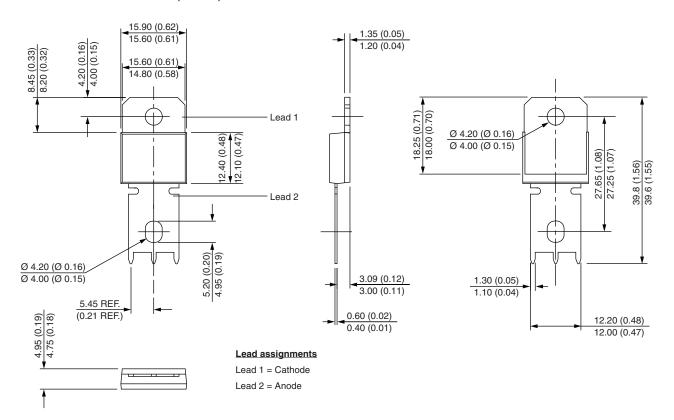
6 - Voltage rating (02 = 200 V)

| LINKS TO RELATED DOCUMENTS | | | | |
|--|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?95240</u> | | | | |
| Part marking information | www.vishay.com/doc?95370 | | | |
| Application note | www.vishay.com/doc?95179 | | | |



PowerTab®

DIMENSIONS in millimeters (inches)





Legal Disclaimer Notice

Vishay

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